WHAT IS CLAIMED IS:

1. A non-volatile memory device, comprising:

an output driver to output a data signal and including:

a pull-up driver including a first pull-up driver having a plurality of P-type transistors and a second pull-up driver having a plurality of N-type transistors; and

a pull-down driver including a plurality of N-type transistors,

wherein one or more power supply voltages having different voltage levels are selectively applied to the pull-up driver,

wherein a first power supply voltage is applied to the first pull-up driver and a second power supply voltage is applied to the second pull-up driver,

wherein the output driver is to be operated based on a pull-up operating signal and a pull-down operating signal received by the output driver, and

at least one of the first pull-up driver and the second pull-up driver in the pull-up driver is to be operated based on frequencies of the pull-up operating signal and the pull-down operating signal.

2. The non-volatile memory device as claimed in claim 1, wherein the first power supply voltage is different from the second power supply voltage.

3. The non-volatile memory device as claimed in claim 1, wherein the first power supply voltage is equal to the second power supply voltage.

4. The non-volatile memory device as claimed in any one of claims 1 to 3, wherein the output driver is to operate at least one of the first pull-up driver and the second pull-up driver based on the voltage levels of the first power supply voltage and the second power supply voltage applied to the pull-up driver.

5. The non-volatile memory device as claimed in claim 4, wherein the plurality of P-type transistors of the first pull-up driver are to be turned OFF based on the voltage levels of the first power supply voltage.

6. The non-volatile memory device as claimed in claim 1, wherein the plurality of P-type transistors of the first pull-up driver are to be turned OFF based on frequency of the pull-up operating signal.

7. The non-volatile memory device as claimed in any one of claims 1 to 6, wherein the pull-down driver includes a plurality of P-type transistors.

8. A non-volatile memory device, comprising:

an output driver to output a data signal; and

an operating signal generator to generate a plurality of operating signals for operating the output driver, wherein the output driver includes:

a pull-up driver including a first pull-up driver having a plurality of P-type transistors and a second pull-up driver having a plurality of N-type transistors, wherein a first power supply voltage is to be applied to the plurality of P-type transistors of the pull-up driver, and a second power supply voltage is to be applied to the plurality of N-type transistors of the pull-up driver; and

a pull-down driver having a plurality of N-type transistors, wherein one or more power supply voltages having different voltage levels are to be selectively applied to the pull-up driver,

wherein the operating signal generator is to receive information regarding the first power supply voltage and the second power supply voltage applied to the pull-up driver, and,

the operating signal generator is to generate the plurality of operating signals based on the information corresponding to the first power supply voltage and the second power supply voltage.

9. The non-volatile memory device as claimed in claim 8, wherein:

the operating signal generator is to generate at least one operating signal to be transmitted to the first pull-up driver, from among the plurality of operating signals to be toggled between a high level and a low level, and

the operating signal generator is to generate at least one operating signal to be transmitted to the second pull-up driver, from among the plurality of operating signals to be toggled between the high level and the low level.

10. The non-volatile memory device as claimed in claim 8 or claim 9, wherein:

the operating signal generator is to generate operating signals to be respectively transmitted to the plurality of P-type transistors in the first pull-up driver, from among the plurality of operating signals to have a high level,

the operating signal generator is to generate at least one operating signal to be transmitted to the second pull-up driver, from among the plurality of operating signals to be toggled between the high level and a low level, and

a voltage level of the high level of the at least one of operating signal to be transmitted to the second pull-up driver is equal to the voltage level of the second power supply voltage.

11. The non-volatile memory device as claimed in any one of claims 8 to 10, wherein the operating signal generator is to receive a clock signal and generate the plurality of operating signals based on a frequency of the clock signal.

12. The non-volatile memory device as claimed in claim 11, wherein:

the operating signal generator is to generate at least one operating signal to be transmitted to the first pull-up driver, from among the plurality of operating signals to be toggled between a high level and a low level, and

the operating signal generator is to generate at least one operating signal to be transmitted to the second pull-up driver, from among the plurality of operating signals to be toggled between the high level and the low level.

13. The non-volatile memory device as claimed in any one of claims 8 to 12, wherein:

the pull-down driver includes a plurality of P-type transistors,

the plurality of P-type transistors correspond to a first pull-down driver, and

the plurality of N-type transistors correspond to a second pull-down driver.

14. A non-volatile memory device, comprising:

an output driver to output a data signal; and

an operating signal generator to generate a plurality of operating signals to operate the output driver, wherein the output driver includes:

a pull-up driver including a first pull-up driver having a plurality of P-type transistors and a second pull-up driver having a plurality of N-type transistors, wherein a first power supply voltage is to be applied to the plurality of P-type transistors of the pull-up driver, and a second power supply voltage is to be applied to the plurality of N-type transistors of the pull-up driver; and

a pull-down driver including a first pull-down driver having a plurality of P-type transistors and a second pull-down driver having a plurality of N-type transistors,

wherein the operating signal generator is to receive information regarding the first power supply voltage and the second power supply voltage applied to the pull-up driver, and

the operating signal generator is to generate the plurality of operating signals based on the information corresponding to the first power supply voltage and the second power supply voltage.

15. The non-volatile memory device as claimed in claim 14, wherein the operating signal generator is to generate a pull-up operating signal to selectively operate at least one of the first pull-up driver and the second pull-up driver and to generate a pull-down operating signal to selectively operate at least one of the first pull-down driver and the second pull-down driver.

16. The non-volatile memory device as claimed in claim 15, wherein the operating signal generator is to selectively operate at least one of the first pull-up driver and the second pull-up driver based on a voltage level of a power supply voltage applied to the pull-up driver.

17. The non-volatile memory device as claimed in claim 15 or claim 16, wherein the operating signal generator is to generate a pull-up operating signal to operate the first pull-up driver and the second pull-up driver and to generate a pull-down operating signal to operate the first pull-down driver and the second pull-down driver.